BIELE-002

B.TECH. IN ELECTRONICS AND COMMUNICATION ENGINEERING (BTECVI) Term-End Examination

December, 2013

BIELE-002 : MICROELECTRONICS TECHNOLOGY

Time : 3 hours

Maximum Marks : 70

- Note: (i) Attempt any seven questions. (ii) Assume suitable missing data, if any.
- 1. (a) How n-type and p-type wafers are identified using flats ? Explain using diagrams. 2x5=10
 - (b) Explain the types of defects in a crystal structure.
- (a) How EGS is prepared from MGS ? Explain with suitable diagrams. 2x5=10
 - (b) Explain the process of crystal growth using CZ technique.
- **3.** Explain the kinetics of oxidation using Deal and **10** Grove's model.
- What is Lithography ? Name different types of 10 Lithography process available. Explain any one process with suitable example.
- What is the use of Etching process in VLSI 10 fabrication ? Name different types of Etching process. Explain the process of Reactive Ion-Beam Etching using suitable diagram.

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- 6. (a) Derive Fick's Laws of diffusion equations.
 - (b) Assume that Boron is diffused into an n-type Si Single Crystal substrate with a doping concentration of 10^{15} atoms/cm³, and also that the diffusion profile can be described by a Gaussian function. Using a diffusion time of 60mins, one obtains a measured junction depth of 2µm and a surface concentration of 1×10^{18} cm⁻³. Find the diffusivity from this impurity profile. 2x5=10
- Explain the process of ion-implantation with 10 suitable schematic diagram. Describe the advantages and disadvantages of high energy implantation.
- 8. Enlist the desired properties of metallization for 10 integrated circuits. What are the applications of metallization ? What are the problems in metallization ?
- What is the need of Epitaxy in IC fabrication ? 10 Discuss the MBE growth system using its schematic diagram.
- 10. Write short notes on **any two** of the followings :
 - (a) CMOS IC technology

2x5 = 10

- (b) Bipolar IC technology
- (c) SOI technology

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